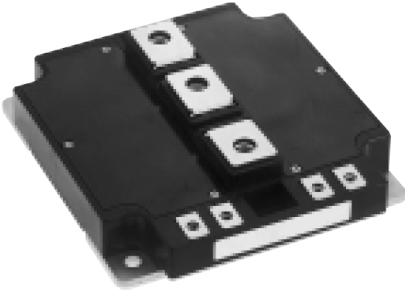


< IGBT MODULES >

# CM800DY-24S

HIGH POWER SWITCHING USE  
INSULATED TYPE



**Dual (Half-Bridge)**

Collector current  $I_C$  ..... **790 A\***  
 Collector-emitter voltage  $V_{CES}$  ..... **1200 V**  
 Maximum junction temperature  $T_{jmax}$  ..... **175 °C**

- Flat base Type
- Copper base plate
- RoHS Directive compliance
- UL Recognized under UL1557, File E323585

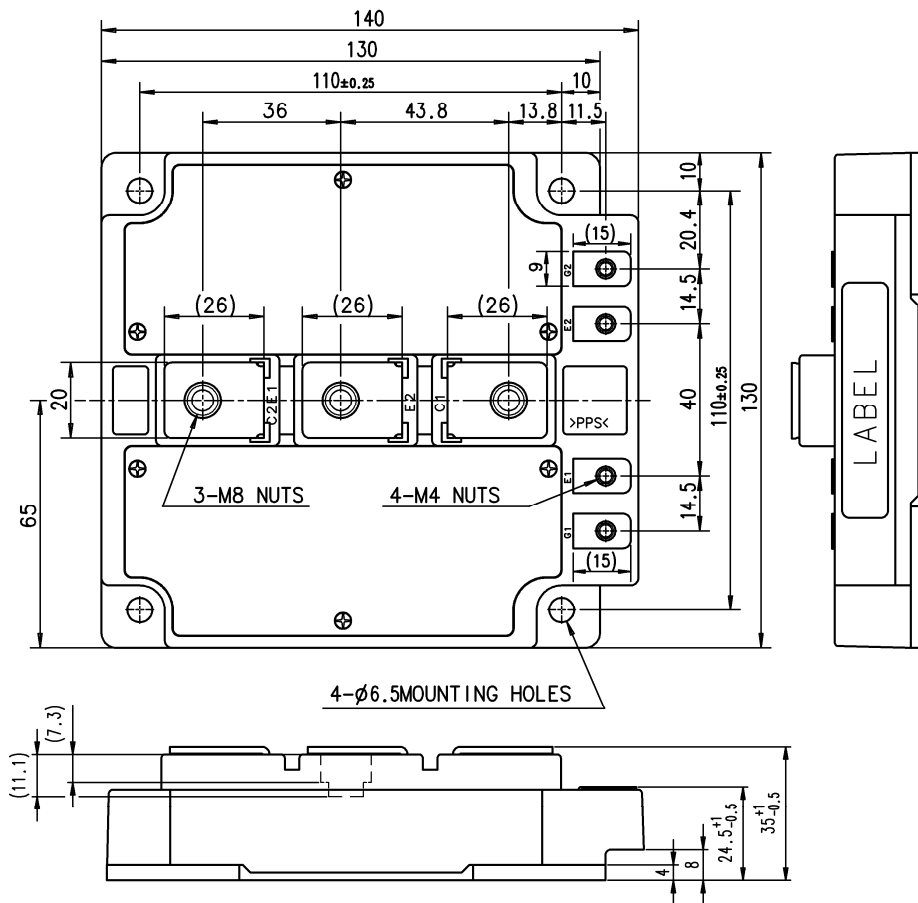
\*. DC current rating is limited by power terminals.

## APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

## OUTLINE DRAWING & INTERNAL CONNECTION

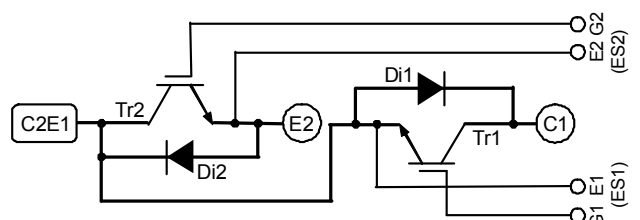
Dimension in mm



Tolerance otherwise specified

Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2

### INTERNAL CONNECTION



< IGBT MODULES >

CM800DY-24S

HIGH POWER SWITCHING USE  
INSULATED TYPE

**ABSOLUTE MAXIMUM RATINGS (T<sub>j</sub>=25 °C, unless otherwise specified)**

Symbol	Item	Conditions	Rating	Unit
V <sub>CES</sub>	Collector-emitter voltage	G-E short-circuited	1200	V
V <sub>GES</sub>	Gate-emitter voltage	C-E short-circuited	±20	V
I <sub>C</sub>	Collector current	DC, T <sub>C</sub> =117 °C (Note.2, 4)	790 *	A
I <sub>CRM</sub>		Pulse, Repetitive (Note.3)	1600	
P <sub>tot</sub>	Total power dissipation	T <sub>C</sub> =25 °C (Note.2, 4)	5355	W
I <sub>E</sub> (Note.1)	Emitter current	T <sub>C</sub> =25 °C (Note.2, 4)	790 *	A
I <sub>ERM</sub> (Note.1)		Pulse, Repetitive (Note.3)	1600	
V <sub>isol</sub>	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	2500	V
T <sub>jmax</sub>	Maximum junction temperature	-	175	°C
T <sub>cmax</sub>	Maximum case temperature	(Note.2)	125	
T <sub>jopr</sub>	Operating junction temperature	-	-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature	-	-40 ~ +125	

**ELECTRICAL CHARACTERISTICS (T<sub>j</sub>=25 °C, unless otherwise specified)**

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I <sub>CES</sub>	Collector-emitter cut-off current	V <sub>CE</sub> =V <sub>CES</sub> , G-E short-circuited	-	-	1.0	mA	
I <sub>GES</sub>	Gate-emitter leakage current	V <sub>GE</sub> =V <sub>GES</sub> , C-E short-circuited	-	-	0.5	µA	
V <sub>GE(th)</sub>	Gate-emitter threshold voltage	I <sub>C</sub> =80 mA, V <sub>CE</sub> =10 V	5.4	6.0	6.6	V	
V <sub>CESat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =800 A (Note.5), V <sub>GE</sub> =15 V, Terminal	T <sub>j</sub> =25 °C	-	1.95	2.40	V
			T <sub>j</sub> =125 °C	-	2.25	-	
			T <sub>j</sub> =150 °C	-	2.35	-	
		I <sub>C</sub> =800 A (Note.5), V <sub>GE</sub> =15 V, Chip	T <sub>j</sub> =25 °C	-	1.70	2.15	V
			T <sub>j</sub> =125 °C	-	1.90	-	
			T <sub>j</sub> =150 °C	-	1.95	-	
C <sub>ies</sub>	Input capacitance	V <sub>CE</sub> =10 V, G-E short-circuited	-	-	80	nF	
C <sub>oes</sub>	Output capacitance		-	-	16		
C <sub>res</sub>	Reverse transfer capacitance		-	-	1.32		
Q <sub>G</sub>	Gate charge	V <sub>CC</sub> =600 V, I <sub>C</sub> =800 A, V <sub>GE</sub> =15 V	-	1868	-	nC	
t <sub>d(on)</sub>	Turn-on delay time	V <sub>CC</sub> =600 V, I <sub>C</sub> =800 A, V <sub>GE</sub> =±15 V, R <sub>G</sub> =0 Ω, Inductive load	-	-	800	ns	
t <sub>r</sub>	Rise time		-	-	200		
t <sub>d(off)</sub>	Turn-off delay time		-	-	600		
t <sub>f</sub>	Fall time		-	-	300		
V <sub>EC</sub> (Note.1)	Emitter-collector voltage	I <sub>E</sub> =800 A (Note.5), G-E short-circuited, Terminal	T <sub>j</sub> =25 °C	-	1.85	2.30	V
			T <sub>j</sub> =125 °C	-	1.85	-	
			T <sub>j</sub> =150 °C	-	1.85	-	
		I <sub>E</sub> =800 A (Note.5), G-E short-circuited, Chip	T <sub>j</sub> =25 °C	-	1.70	2.15	V
			T <sub>j</sub> =125 °C	-	1.70	-	
			T <sub>j</sub> =150 °C	-	1.70	-	
t <sub>rr</sub> (Note.1)	Reverse recovery time	V <sub>CC</sub> =600 V, I <sub>E</sub> =800 A, V <sub>GE</sub> =±15 V, R <sub>G</sub> =0 Ω, Inductive load	-	-	300	ns	
Q <sub>rr</sub> (Note.1)	Reverse recovery charge	R <sub>G</sub> =0 Ω, Inductive load	-	42.8	-	µC	
E <sub>on</sub>	Turn-on switching energy per pulse	V <sub>CC</sub> =600 V, I <sub>C</sub> =I <sub>E</sub> =800 A, V <sub>GE</sub> =±15 V, R <sub>G</sub> =0 Ω,	-	107	-	mJ	
E <sub>off</sub>	Turn-off switching energy per pulse	T <sub>j</sub> =150 °C, Inductive load	-	82	-		
E <sub>rr</sub> (Note.1)	Reverse recovery energy per pulse	T <sub>j</sub> =150 °C, Inductive load	-	71	-	mJ	
R <sub>CC'+EE'</sub>	Internal lead resistance	Main terminals -chip, per switch, T <sub>C</sub> =25 °C	-	-	0.4	mΩ	
r <sub>G</sub>	Internal gate resistance	Per switch	-	2.45	-	Ω	

< IGBT MODULES >  
**CM800DY-24S**  
**HIGH POWER SWITCHING USE**  
**INSULATED TYPE**

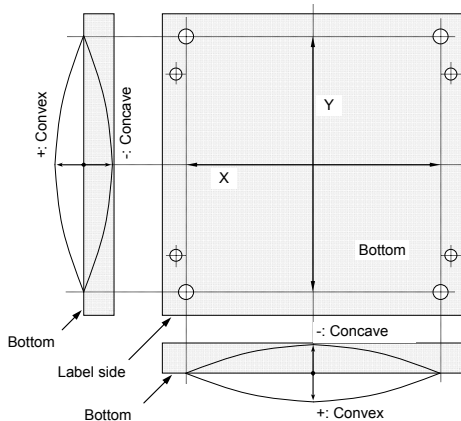
**THERMAL RESISTANCE CHARACTERISTICS**

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance (Note.2)	Junction to case, per IGBT	-	-	28	K/kW
$R_{th(j-c)D}$		Junction to case, per FWDi	-	-	45	K/kW
$R_{th(c-s)}$	Contact thermal resistance (Note.2)	Case to heat sink, per 1/2 module, Thermal grease applied (Note.6)	-	15	-	K/kW

**MECHANICAL CHARACTERISTICS**

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$M_t$	Mounting torque	Main terminals M 8 screw	8.8	9.8	10.8	N·m
		Auxiliary G/Es Terminals M 4 screw	1.3	1.5	1.7	
$M_s$		Mounting to heat sink M 6 screw	3.5	4.0	4.5	N·m
m	Weight	-	-	1200	-	g
$e_c$	Flatness of base plate	On the centerline X, Y (Note.7)	-100	-	+100	$\mu$ m

- Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (FWDi).  
 2. Case temperature ( $T_c$ ) and heat sink temperature ( $T_s$ ) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.  
 The heat sink thermal resistance should measure just under the chips.  
 3. Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) dose not exceed  $T_{jmax}$  rating.  
 4. Junction temperature ( $T_j$ ) should not increase beyond  $T_{jmax}$  rating.  
 5. Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.  
 6. Typical value is measured by using thermally conductive grease of  $\lambda=0.9$  W/(m·K).  
 7. Base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



\*. DC current rating is limited by power terminals.

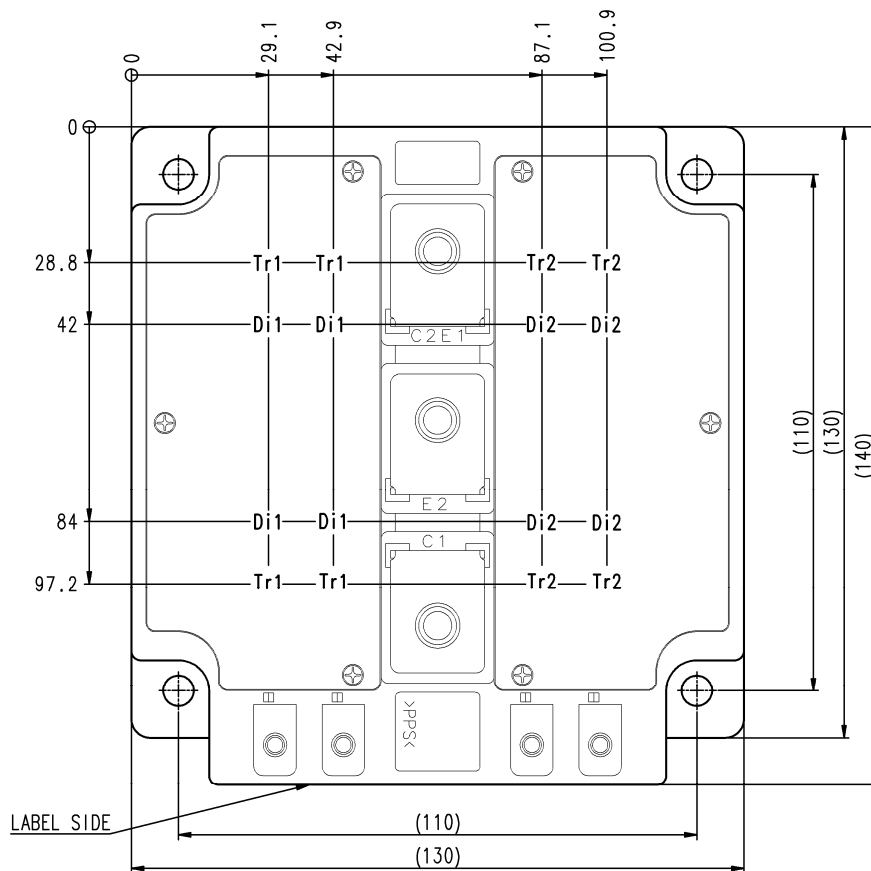
**RECOMMENDED OPERATING CONDITIONS**

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{CC}$	(DC) Supply voltage	Applied across C1-E2	-	600	850	V
$V_{GEon}$	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2	13.5	15.0	16.5	V
$R_G$	External gate resistance	Per switch	0	-	5.1	$\Omega$

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**CM800DY-24S**  
 HIGH POWER SWITCHING USE  
 INSULATED TYPE

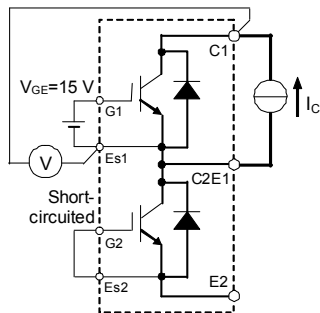
CHIP LOCATION (Top view)

Dimension in mm, tolerance:  $\pm 1$  mm



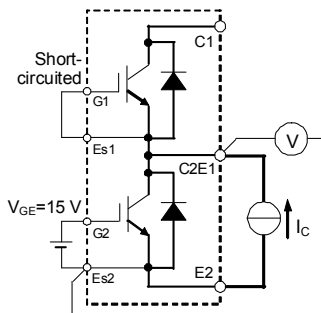
Tr1/Tr2: IGBT, Di1/Di2: FWDi

**TEST CIRCUIT**

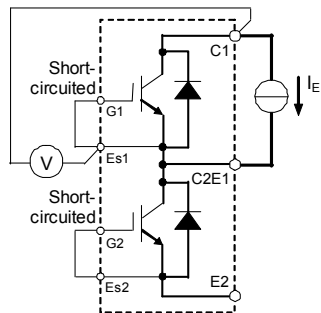


Tr1

$V_{CEsat}$  test circuit

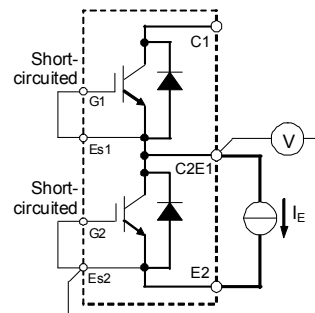


Tr2



Di1

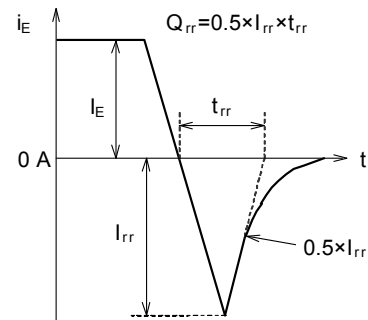
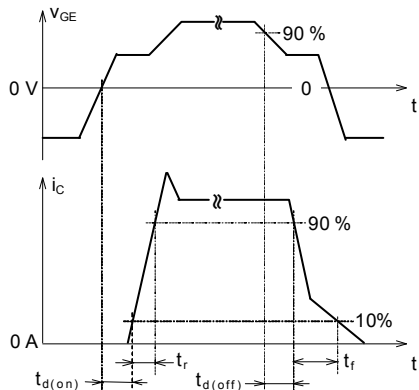
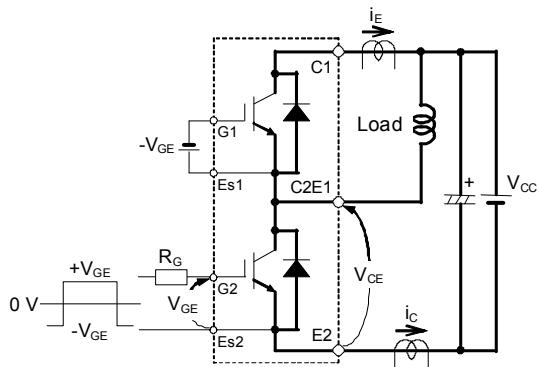
$V_{EC}$  test circuit



Di2

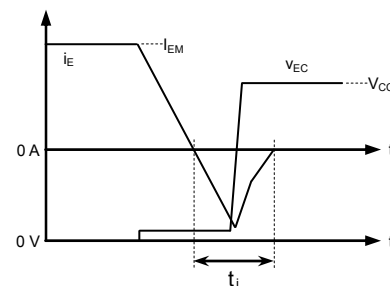
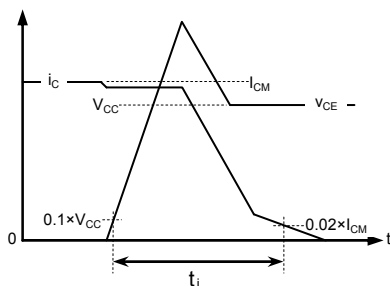
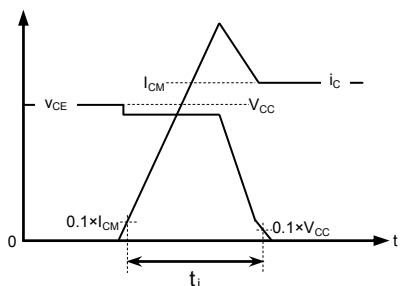
< IGBT MODULES >  
**CM800DY-24S**  
 HIGH POWER SWITCHING USE  
 INSULATED TYPE

**TEST CIRCUIT AND WAVEFORMS**



**Switching characteristics test circuit and waveforms**

**$t_{rr}$ ,  $Q_{rr}$  test waveform**



**IGBT Turn-on switching energy**

**IGBT Turn-off switching energy**

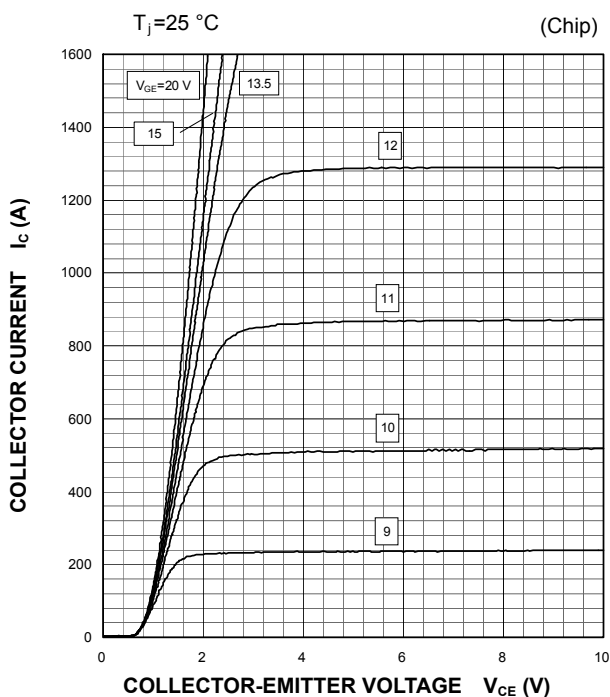
**FWDI Reverse recovery energy**

**Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)**

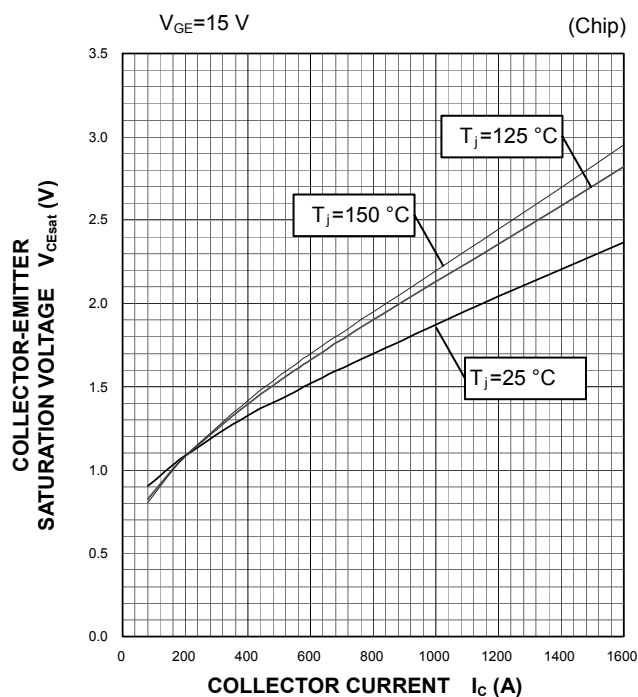
< IGBT MODULES >  
**CM800DY-24S**  
 HIGH POWER SWITCHING USE  
 INSULATED TYPE

PERFORMANCE CURVES

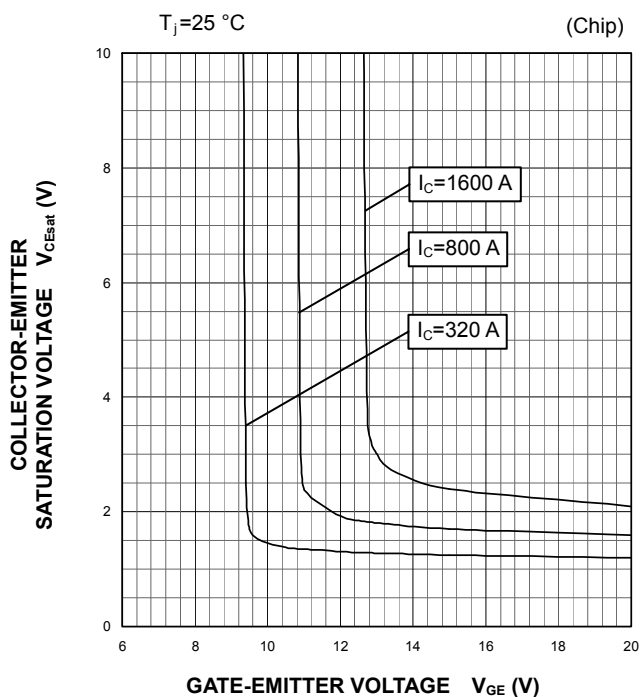
OUTPUT CHARACTERISTICS  
 (TYPICAL)



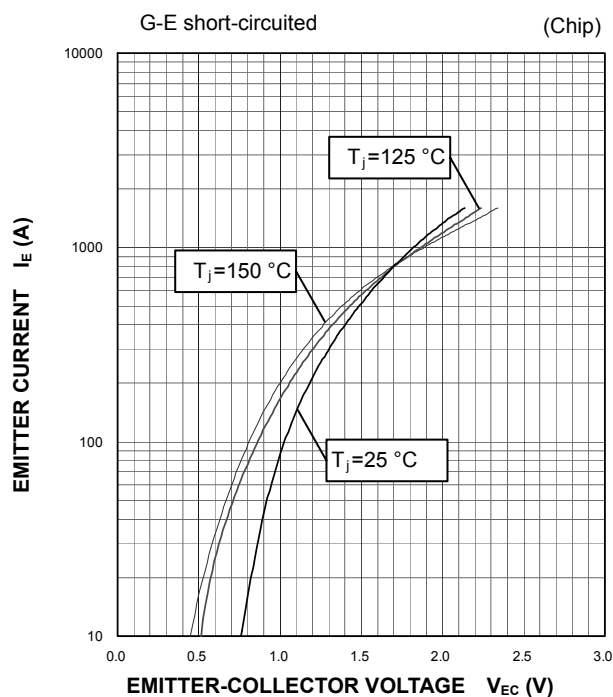
COLLECTOR-EMITTER SATURATION  
 VOLTAGE CHARACTERISTICS  
 (TYPICAL)



COLLECTOR-EMITTER SATURATION  
 VOLTAGE CHARACTERISTICS  
 (TYPICAL)



FREE WHEELING DIODE  
 FORWARD CHARACTERISTICS  
 (TYPICAL)

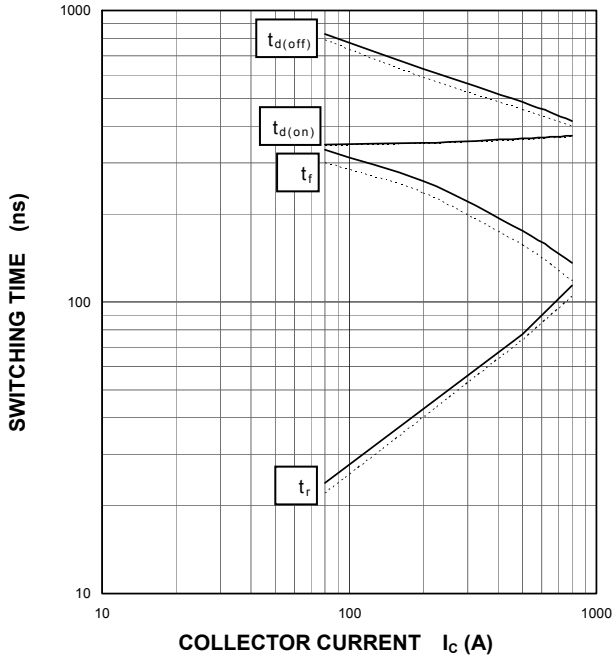


< IGBT MODULES >  
**CM800DY-24S**  
 HIGH POWER SWITCHING USE  
 INSULATED TYPE

PERFORMANCE CURVES

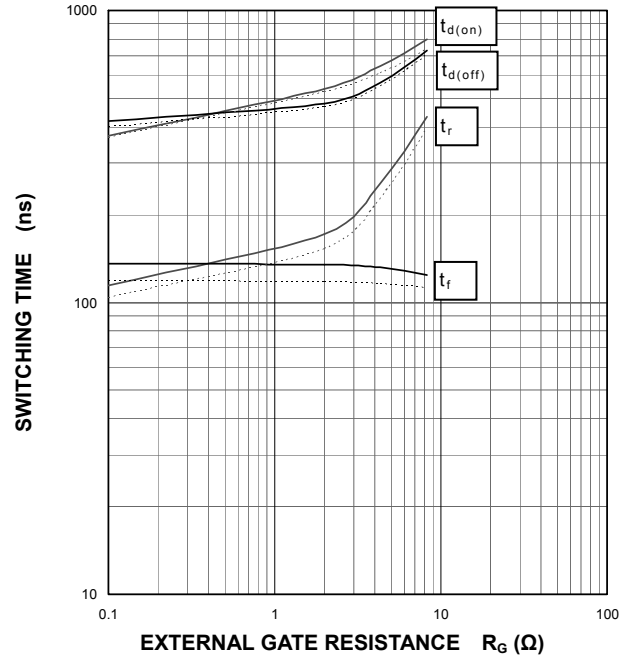
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=0\ \Omega$ , INDUCTIVE LOAD  
 —:  $T_J=150\text{ }^\circ\text{C}$ , - - - -:  $T_J=125\text{ }^\circ\text{C}$



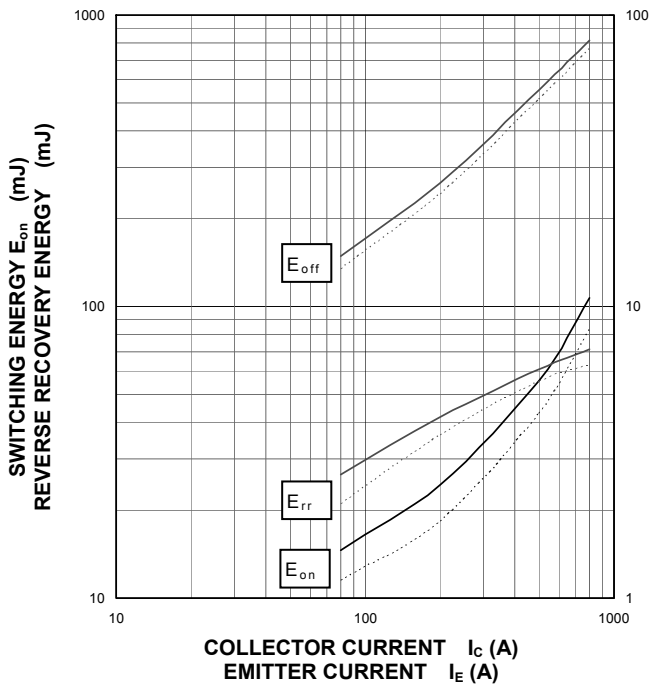
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**

$V_{CC}=600\text{ V}$ ,  $I_C=800\text{ A}$ ,  $V_{GE}=\pm 15\text{ V}$ , INDUCTIVE LOAD  
 —:  $T_J=150\text{ }^\circ\text{C}$ , - - - -:  $T_J=125\text{ }^\circ\text{C}$



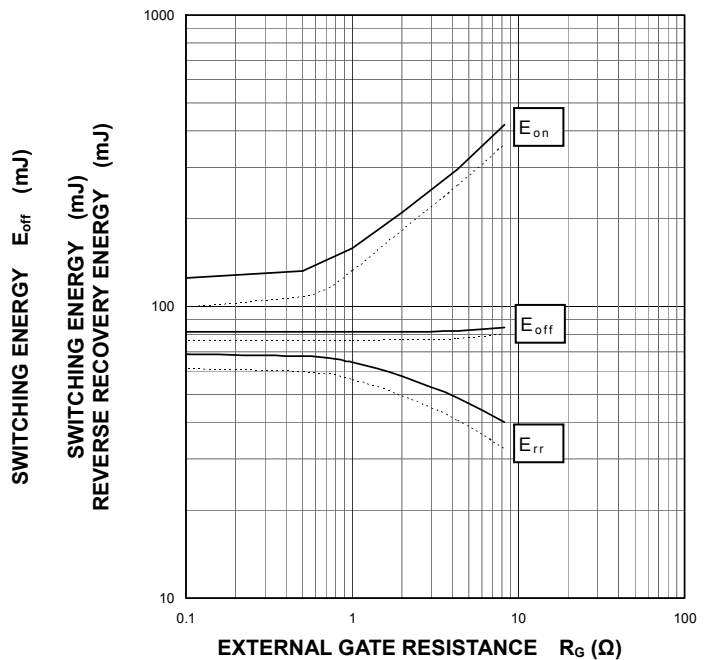
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=0\ \Omega$ ,  
 INDUCTIVE LOAD, PER PULSE  
 —:  $T_J=150\text{ }^\circ\text{C}$ , - - - -:  $T_J=125\text{ }^\circ\text{C}$



**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**

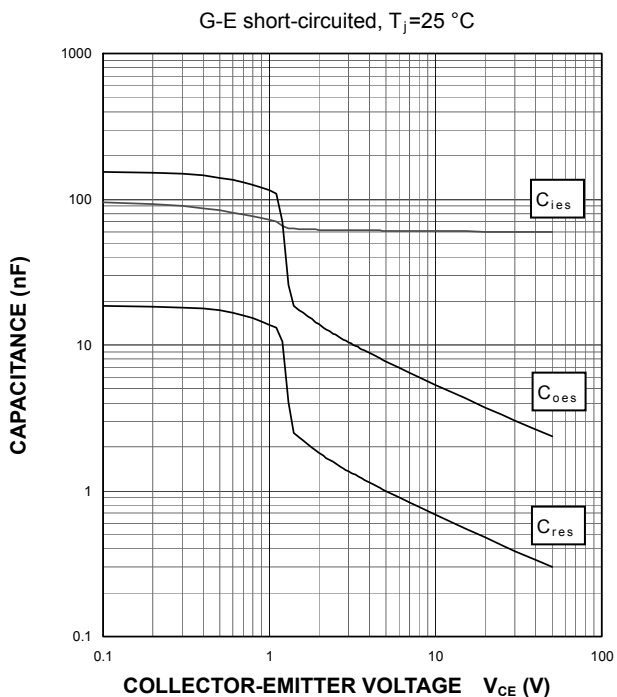
$V_{CC}=600\text{ V}$ ,  $I_C/I_E=800\text{ A}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  
 INDUCTIVE LOAD, PER PULSE  
 —:  $T_J=150\text{ }^\circ\text{C}$ , - - - -:  $T_J=125\text{ }^\circ\text{C}$



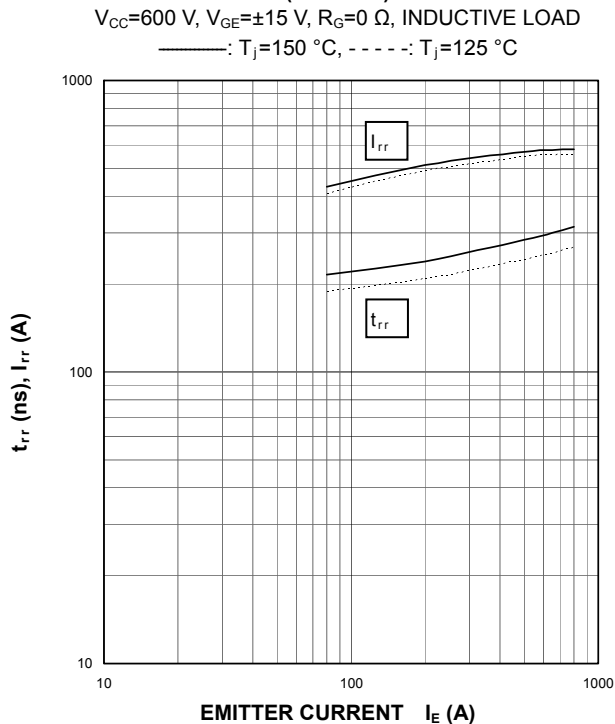
< IGBT MODULES >  
**CM800DY-24S**  
 HIGH POWER SWITCHING USE  
 INSULATED TYPE

PERFORMANCE CURVES

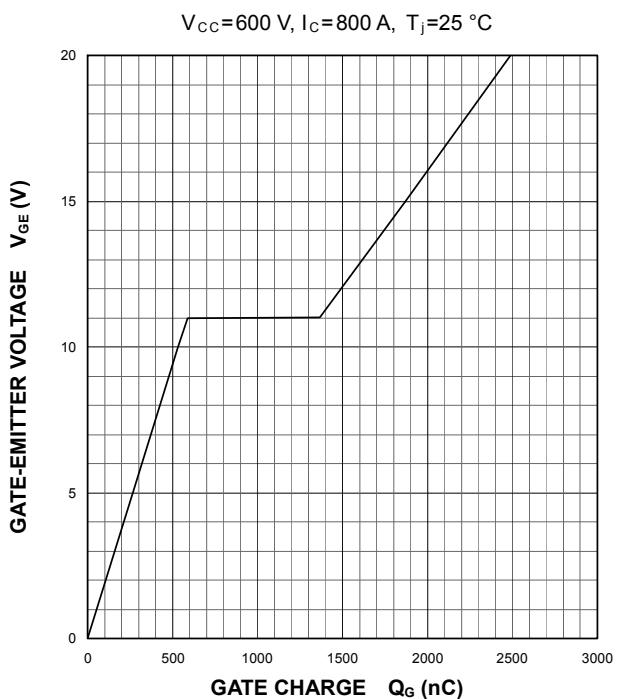
**CAPACITANCE CHARACTERISTICS (TYPICAL)**



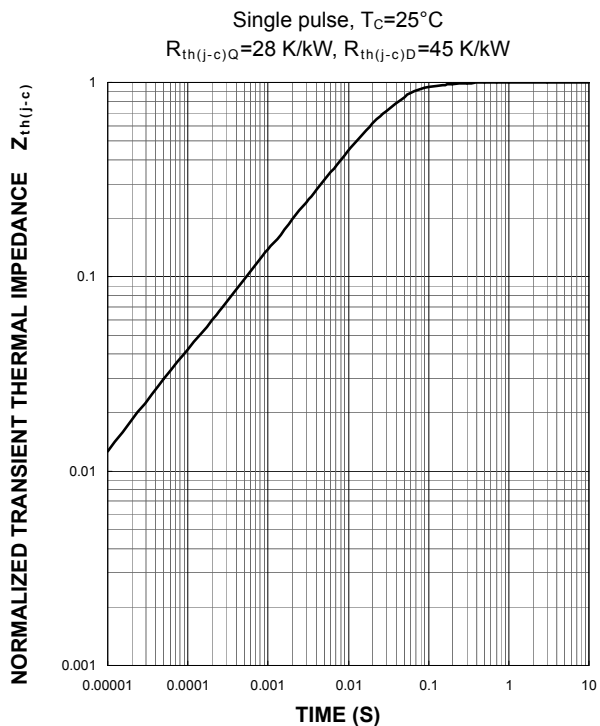
**FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)**



**GATE CHARGE CHARACTERISTICS (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)**





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